

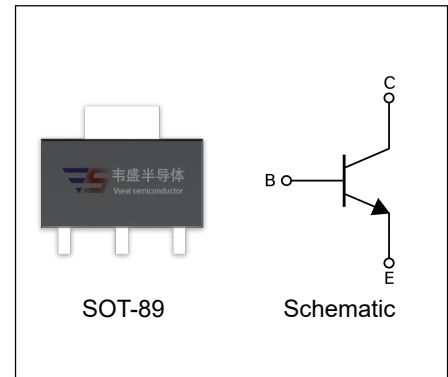
2SC1766 TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage

APPLICATIONS

- Power Amplifier



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	2	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	82		390	
	$h_{FE(2)}^*$	$V_{CE}=2V, I_C=2A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1A, I_B=50mA$			1.2	V
Transition frequency	f_T	$V_{CE}=2V, I_C=0.5A, f=100MHz$		120		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	P	Q	Y
RANGE	82 - 180	120 - 270	180 - 390

*Pulse test: pulse width $\leq 300\mu s$, duty cycles $\leq 2.0\%$.

Static Characteristic
